

**IN THE CLAIMS:**

1. (Currently Amended) A method of manufacturing a display device comprising:  
forming a thin film transistor over a substrate;  
forming an electrode which is electrically connected with the thin film transistor; and  
forming a thin film over the electrode with an electron beam evaporation method,  
wherein an acceleration voltage of electrons of the electron beam evaporation method  
is controlled to become the acceleration voltage such that by which the thin film transistor is  
not deteriorated with radial rays radiated from an evaporation material for forming the thin  
film when the evaporation material is irradiated with an electron beam, and  
wherein increase of a sub-threshold coefficient of the thin film transistor is prevented  
by controlling the acceleration voltage of electrons.

2. (Currently Amended) A method of manufacturing a display device comprising:  
forming a thin film transistor over a substrate;  
forming an electrode which is electrically connected with the thin film transistor; and  
forming a thin film over the electrode with an electron beam evaporation method,  
wherein an acceleration voltage of electrons of the electron beam evaporation method  
is controlled to become the acceleration voltage such that by which the thin film transistor is  
not deteriorated with radial rays radiated from an evaporation material for forming the thin  
film when the evaporation material is irradiated with an electron beam.

3. (Currently Amended) A method of manufacturing a display device comprising:  
forming a thin film transistor over a substrate;  
forming a first electrode which is electrically connected with the thin film transistor;  
forming a light emitter containing an organic compound over the first electrode; and  
forming a second electrode over the light emitter with an electron beam evaporation  
method,  
wherein an acceleration voltage of electrons of the electron beam evaporation method  
is controlled to become the acceleration voltage such that by which the thin film transistor is  
not deteriorated with radial rays radiated from an evaporation material for forming the second  
electrode when the evaporation material is irradiated with an electron beam, and

wherein increase of a sub-threshold coefficient of the thin film transistor is prevented by controlling the acceleration voltage of electrons.

4. (Currently Amended) A method of manufacturing a display device comprising:  
forming a thin film transistor over a substrate;  
forming a first electrode which is electrically connected with the thin film transistor;  
forming a light emitter containing an organic compound over the first electrode; and  
forming a second electrode over the light emitter with an electron beam evaporation method,

wherein an acceleration voltage of electrons of the electron beam evaporation method is controlled to become the acceleration voltage such that by which the thin film transistor is not deteriorated with radial rays radiated from the evaporation material for forming the second electrode when the evaporation material is irradiated with an electron beam.

5. (Previously Presented) A method of manufacturing a display device comprising:  
forming a thin film transistor over a substrate;  
forming an electrode which is electrically connected with the thin film transistor; and  
forming a thin film over the electrode with an electron beam evaporation method,  
wherein a thickness of the thin film is 0.1  $\mu\text{m}$  or less, and  
wherein control is performed such that a time during which, the thin film transistor is exposed to radial rays radiated from an evaporation material for forming the thin film, is shortened to avoid deterioration of the thin film transistor when the evaporation material is irradiated with an electron beam.

6. (Previously Presented) A method of manufacturing a display device comprising:  
forming a thin film transistor over a substrate;  
forming a first electrode which is electrically connected with the thin film transistor;  
forming a light emitter containing an organic compound over the first electrode; and  
forming a second electrode over the light emitter with an electron beam evaporation method,  
wherein a thickness of the second electrode is 0.1  $\mu\text{m}$  or less, and

wherein control is performed such that a time during which, the thin film transistor is exposed to radial rays radiated from an evaporation material for forming the second electrode, is shortened to avoid deterioration of the thin film transistor when the evaporation material is irradiated with an electron beam.

7. (Original) A method of manufacturing a display device according to claim 1, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

8. (Original) A method of manufacturing a display device according to claim 2, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

9. (Original) A method of manufacturing a display device according to claim 3, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

10. (Original) A method of manufacturing a display device according to claim 4, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

11. (Original) A method of manufacturing a display device according to claim 5, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

12. (Original) A method of manufacturing a display device according to claim 6, wherein a multi-component alloy or compound, which is constituted of a metal component and a component containing either or both of alkali metal and alkali earth metal, is used as the evaporation material.

13. (Previously Presented) A method of manufacturing a display device according to claim 1, wherein radial rays are not substantially radiated from the evaporation material for forming the thin film when the evaporation material is irradiated with the electron beam.

14. (Previously Presented) A method of manufacturing a display device according to claim 2, wherein radial rays are not substantially radiated from the evaporation material for forming the thin film when the evaporation material is irradiated with the electron beam.

15. (Previously Presented) A method of manufacturing a display device according to claim 3, wherein radial rays are not substantially radiated from the evaporation material for forming the thin film when the evaporation material is irradiated with the electron beam.

16. (Previously Presented) A method of manufacturing a display device according to claim 4, wherein radial rays are not substantially radiated from the evaporation material for forming the thin film when the evaporation material is irradiated with the electron beam.

17. (New) A method of manufacturing a display device according to claim 5, wherein increase of a sub-threshold coefficient of the thin film transistor is prevented by controlling an acceleration voltage of electrons of the electron beam.

18. (New) A method of manufacturing a display device according to claim 6, wherein increase of a sub-threshold coefficient of the thin film transistor is prevented by controlling an acceleration voltage of electrons of the electron beam.

19. (New) A method of manufacturing a display device according to claim 5, further comprising forming a metal film over the thin film by a resistance heating evaporation method or sputtering method.

20. (New) A method of manufacturing a display device according to claim 6, further comprising forming a metal film over the second electrode by a resistance heating evaporation method or sputtering method.